



## 2SA671

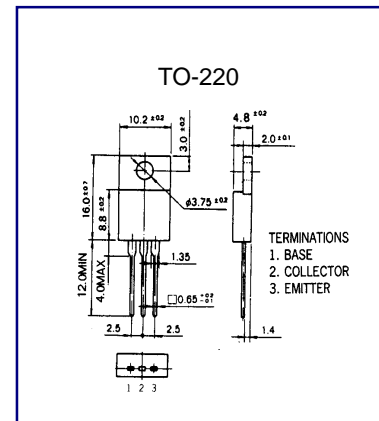
## PNP EPITAXIAL SILICON TRANSISTOR

### LOW FREQUENCY POWER AMPLIFIER

- Complement to 2SC1061

### ABSOLUTE MAXIMUM RATINGS ( $T_A=25^\circ\text{C}$ )

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V <sub>CB0</sub>	-50	V
Collector-Emitter Voltage	V <sub>CE0</sub>	-50	V
Emitter-Base voltage	V <sub>EB0</sub>	-5	V
Collector Current (DC)	I <sub>C</sub>	-3	A
Collector Dissipation (T <sub>c</sub> =25°C)	P <sub>C</sub>	25	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-50~150	°C



### ELECTRICAL CHARACTERISTICS ( $T_A=25^\circ\text{C}$ )

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> =-50V, I <sub>E</sub> =0			-10	μA
Emitter Cutoff Current	I <sub>EB0</sub>	V <sub>EB</sub> =-5V, I <sub>C</sub> =0			10	μA
DC Current Gain	h <sub>FE1</sub>	V <sub>CE</sub> =-4V, I <sub>C</sub> =-1A	35		200	
Collector- Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-3A, I <sub>B</sub> =-0.3A			-1.0	V
Current Gain Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> =-2V, I <sub>C</sub> =-0.5A		8		MHZ